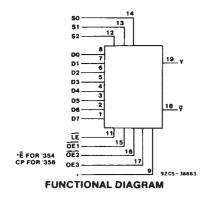
File Number 1690



High-Speed CMOS Logic



8-Input Multiplexer/Register, 3-State

CD54/74HC/HCT354 — Transparent Data & Select Latches CD54/74HC/HCT356 — Edge-Triggered Data Flip-Flops Transparent Select Latches

Type Features:

- Buffered inputs
- 3-State Complementary Outputs
- Bus Line Driving Capability
- Typical propagation delay: V_{CC} = 5V, C_L = 15 pF, T_A = 25°C Data to Output (354) = 18 ns Clock to Output (356) = 22 ns

The RCA-CD54/74HC/HCT354 and CD54/74HC/HCT356 are data selectors/multiplexers that select one of eight sources. In both the HC/HCT354 and HC/HCT356 the data select bits S0, S1, and S2 are stored in transparent latches that are enabled by a low latch enable input, $\overline{\text{LE}}$.

In the HC/HCT354 the data enable input, \overline{E} , controls transparent latches that pass data to the outputs when \overline{E} is high and latches in new data when \overline{E} is low.

In the HC/HCT356 the data is stored in edge-triggered flipflops that are triggered by a low-to-high clock transition.

In both types the three-state outputs are controlled by three output-enable inputs OE1, OE2, and OE3.

The CD54HC/HCT354/356 are supplied in 20-lead ceramic dual-in-line packages (F suffix). The CD74HC/HCT354/356 are supplied in 20-lead plastic dual-in-line plastic packages (E suffix). The CD54/74HC/HCT354/356 are also supplied in chip form (H suffix). The CD74HC/HCT354/356 are also available in plastic surface mounted packages (M suffix).

Family Features:

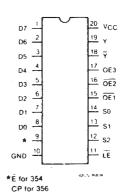
- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
 - Balanced Propagation Delay and Transition Times
 Significant Power Reduction Compared to LSTTL Logic ICs
 - Alternate Source is Philips/Signetics
 - CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity:
 - $N_{\rm iL} = 30\%$, $N_{\rm iH} = 30\%$ of $V_{\rm CC}$; @ $V_{\rm CC} = 5~V$ \blacksquare CD54HCT/CD74HCT Types:
 - 4.5 to 5.5 V Operation

 Direct LSTTL Input Logic Compatibility

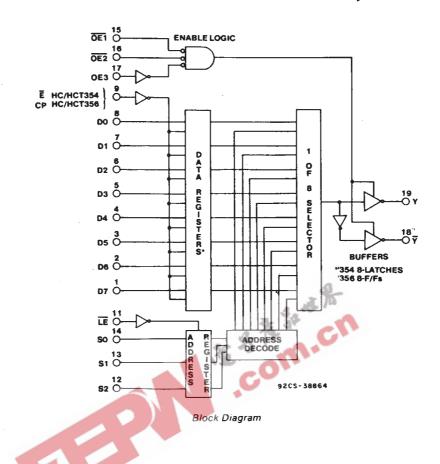
 V_{IL} = 0.8 V Max., V_{IM} = 2 V Min.

 CMOS Input Compatibility

 I₁ ≤ 1 µA @ V_{OL}, V_{OH}



TERMINAL ASSIGNMENT

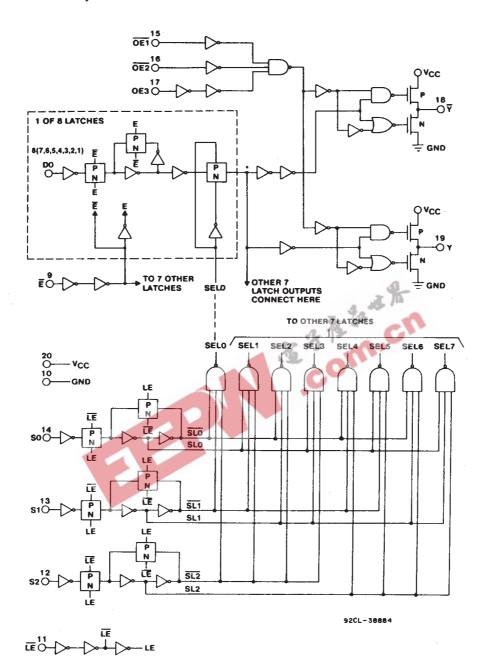


TRUTH TABLE

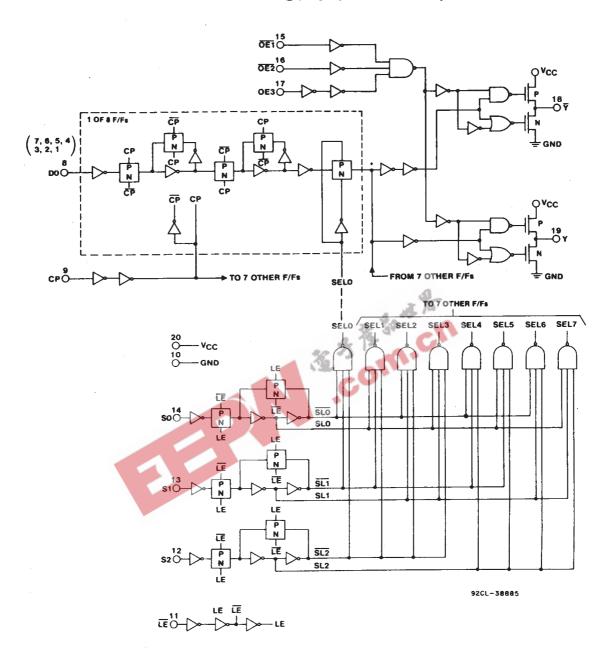
			Inp	uts					
s	elect #		Enable Data 'HC354 'HCT354	Clock 'HC356 'HCT356		Outpu Enable		Outp	outs
S2	S1	SO	E	СР	ŌĒ1	ŌE2	OE3	Y	Υ
Х	Х	Х	Х	Х	Н	Х	Х	Z	Z
Х	Х	X	×	X	X	Н	X	Z	Z
Х	Х	Х	×	×	X	Х	L	Z	Z
L	L	L	L	_~	L	L	H	D0	D0
L	L	L	н	HorL	L	L	H	DO _n	D0 _n
L	L	Н	L		L	L	Н	D1	D1
L	L	Н	н	HorL	L	L	H	D1 _n	D1 _n
L	Н	L	L	· ~	L	L	H	D2	D2
L	Н	L	н	HorL	L	L	Н	D2 _n	D2 _n
L.	Н	Н	L	~	Ł	L	Н	D3	D3
L	Н	+!	н	HorL	L	Ł	H	D3,	D3 _n
Н	L	L	L	_	L	Ĺ	Н	D4	D4
н	L	L	н	HorL	L	Ł	Н	D4 _n	D4 _n
н	L	Н	L	~	L	Ł	Н	D5	D5
н	L	Н	н	HorL	L	L	н	D5 ₀	D5 _n
н	Н	L	L		L	Ł	н	D6	D6
н	Н	L	н	Hort	L	Ļ	н	D ₆	D6,
Н	Н	Н	Ł		L	L	H	D 7	D7
Н	H	Н	н	HorL	L	L	н	D7 ₀	D7 _n

Notes

- ... D7_n = the level of steady state inputs D0 through D7, respectively, before the most recent low-to-high transition of data control
- or clock
 # This column shows the input address setup with LE low



HC/HCT354 Logic Diagram



HC/HCT356 Logic Diagram

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Voc)	· ·
(Voltages referenced to ground)	-0.5 to +7V
DC INPUT DIODE CURRENT, I_{iK} (FOR V, $<$ -0.5 V OR V, $>$ V _{CC} + 0.5V)	±20mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR V_{ν} < -0.5 V OR V_{ν} > 0.5 V +V	cc) ±20mA
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V $<$ Vo $<$ Vcc $+$ 0.5	5V) ±35mA
DC V _{cc} OR GROUND CURRENT (I _{cc})	±70mA
POWER DISSIPATION PER PACKAGE (Pp):	· · · · · · · · · · · · · · · · · · ·
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	
For T _A = -40 to +70° C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	
STORAGE TEMPERATURE (Tsig)	
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max.	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	4 35-11
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	IITS	LIAUTO	
	MIN.	MAX.	UNITS	
Supply-Voltage Range (For T _A = Full Package Temperature Range)				
CD54/74HC Types	2	6		
CD54/74HCT Types	4.5	5.5	V	
DC Input or Output Voltage V _I , V _O	0	V _{CC}	V	
Operating Temperature T _A :			1	
CD74 Types	-40	+85	l ∘c	
CD54 Types	-55	+125		
Input Rise and Fall Times t _{r.} t _f				
at 2 V	0	1000		
at 4.5 V	l 0	500	ns	
at 6 V	lő	400		

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

	HC35	1/356/	CD54	IHC35	4/356	3	_		С	D74H	CT354	4/356/	/CD54	нст	354/3	CD74HCT354/356/CD54HCT354/356								
		TEST IDITIONS		F	IC/54 TYPE		741 TY		541 TY		TEST		1	CT/54 TYPE		74HCT TYPE		54HCT TYPE						
CHARACTERISTIC	۷,	l ₀	Vcc	,	25° C	;	1	o/ i°C	-5 +12		V,	Vcc		+25° C		1	0/ 5°C	-5 +12	5/ 5°C	UNITS				
	v	mA.	٧	Min	Тур	Max	Min	Max	Min	Max	٧	٧	Min	Тур	Max	Min	Max	Min	Max					
High-Level			2	1.5	_	_	1.5		1.5			4.5												
Input Voltage V _{IH}			4.5	3.15	_	-	3.15	_	3.15	_	_	to	2	–	_	2	-	2	_	٧				
			6	4.2	_	-	4.2	_	4.2	_	<u> </u>	5.5												
Low-Level			2	_	_	0.5	_	0.5	-	0.5		4.5												
Input Voltage V _{IL}			4.5	-	-	1.35	-	1.35	-	1.35	-	to	_		0.8	-	0.8	_	8.0	٧				
			6		1	1.8	_	1.8	_	1.8	A 18	5,5			<u> </u>									
High-Level	V _{IL}		2	1.9	_	_	1.9	_	1.9	-73	Vic		0											
Output Voltage V _{OH}	or	-0.02	4.5	4.4			4.4	-3	4.4	5-1	10	4.5	4.4	-	_	4.4	-	4.4	-	v				
CMOS Loads	V _H		6	5.9			5.9	7.3	5.9	_7	$V_{\rm tot}$													
	Vir				7						V _{IL}													
TTL Loads	or	-6	4.5	3.98		1-1	3.84	7	3.7		or	4.5	3.98	-	-	3.84	-	3.7	-	٧				
(Bus Driver)	V _{int}	-7.8	6	5.48	Ň	_	5.34		5.2		V _{iH}						ļ							
Low-Level	V _{IL}		2	_	_	0.1	_	0.1	_	0.1	٧٠													
Output Voltage Vol.	or	0.02	4.5	_	_	0.1		0.1	-	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	v				
CMOS Loads	V _{H1}		6	_	_	0.1	_	0.1		0.1	V _{iid} *	_							ļ					
	Vic										V _{IL}													
TTL Loads	or	6	4.5	_	-	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	V				
(Bus Driver)	V _{IH}	7.8	6		-	0.26	_	0.33	_	0.4	V _{IH}				<u> </u>				<u> </u>					
Input Leakage	V _{cc}										Any Voltage													
Current I	or		6	-		±0.1	_	±1	-	±1	Between	5.5	-	-	±0.1	-	±1		±1	μΑ				
	Gnd			<u></u>							V _{cc} & Gnd				L			_						
Quiescent	V _{cc}										V _{cc}													
Device	or	0	6	_	-	8	-	80	_	160	or	5.5	-	-	8	-	80	-	160	μΑ				
Current I _{cc}	Gnd						L_	L.			Gnd	L			<u> </u>			_	<u> </u>					
Additional Quiescent Device Current per input pin: 1 unit load								•			V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	-	490	μΑ				
3-State Leakage Current loz	V _{IL} or V _H	V _o = V _{cc} or Gnd	6	_	_	±0.5	_	±5.0		±10	V _{IL} Of V _{IH}	5.5	-	_	±0.5	-	±5.0		±10	μΑ				

^{*}For dual-supply systems theoretical worst case (V_i = 2.4 V_c V_{CC} = 5.5 V) specification is 1.8 mA.

HCT354 Input Loading Table

Input	Unit Loads*
D0-D7	0.50
S0, S1, S3	0.70
OE1, OE2	0.80
OE3	0.25
ΪĒ	0.25
Ē	0.60

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25°C.

HCT356 Input Loading Table

Input	Unit Loads*
D0-D7	0.50
S0, S1, S3	0.70
ŌĒ1, ŌĒ2	0.80
OE3	0.25
<u>LE</u>	0.25
СР	0.60

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, input t, t, = 6 ns) - HC/HCT354

CHARACTERISTIC	CL	SYMBOL	TYP	UNITS	
OTATIO TENOTIO	(pF)	SIMBOL	54/74HC	54/74HCT	OMITS
Propagation Delay Dn → Y, ♥	15	t _{PLH} , t _{PHL}	18	20	ns
Ē →Y, Ÿ	15	t _{PLH} , t _{PHL}	21	23	ns
Sn-→ Y, Ÿ	15	telh, tehl	22	25	ns
LE →Y, Ÿ	15	t _{PLH} , t _{PHL}	24	25	ns
Output Disabling Time	15	t _{PLZ} , t _{PHZ}	13	13, 16	ns
Output Enabling Time	15	tezi, tezh	12, 13	14	ns
Power Dissipation Capacitance*		C _{PD}	90	92	рF

^{*}CPD is used to determine the dynamic power consumption, per device.

PREREQUISITE FOR SWITCHING FUNCTION — HC/HCT354

				25	°C		-4	0°C to	o +85°	,C	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	Н	C	H	CT	74	НС	74t	ICT	54	HC	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
E pulse width		2	80	-	_	_	100	_	_	<u> </u>	120	_	_	_	
	t _{PLH} •	4.5	16	_	16	_	20	—	20	_	24	-	24	_	ns
	t _{PHL}	6	14	_			17	_	_	_	20	_			
LE pulse width		2	80	_	-	_	100	_		T-	120	_	_	_	
	t _{PLH}	4.5	16	_	16		20		20	_	24	—	24	—	ns
	t _{PHL}	6	14		_	—	17	_	—	—	20	_	[—		
Set Up Times		2	50	_	_	_	65	_	_	_	75	_		_	
Dn → Ē	tsu	4.5	10	_	10	_	13		13	<u> </u>	15	-	15	l —	ns
		6	9	_			11	_	_	_	13	_	_	_	
		2	50	_		—	65		_	_	75	l —	_	_	
Sn → LE	tsu	4.5	10	_	10		13	_	13	_	15	_	15	-	ns
	<u> </u>	6	9		_	_	11		_		13		_		
Hold Times		2	45	_	_		55	_	_	_	70	_			
Dn → Ē	tн	4.5	9		9	_	11		11	_	14		14		ns
		6	8		_	_	9		_	_	12	_	_	_	
		2	45	_	_	_	55			_	70	_	_	_	
Sn → LE	ŧн	4.5	9	_	9	_	11		11.		14	-	14	_	ns
		6	8	_	_		9	-	_	_	12				

 $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where:

f_i = input frequency,

C_L = output load capacitance.

V_{cc} = supply voltage

SWITCHING CHARACTERISTICS (CL = 50 pF, Input to t = 6 ns) - HC/HCT354

				25	°C		-4	0°C t	+85°	С		5°C to			
CHARACTERISTIC	SYMBOL	Vcc	Н	C	Н	CT	741	HC	74H	ICT	541	HC	54H		UNITS
		-	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.		Min.	Max.	
Propagation Delay,	tpLH	2	—	210	_		_	265	_	_	_	315	—	—	
Dn → Y, \overline{Y}	t _{PHL}	4.5	_	42		47	_	53	-	59	_	63	—	71	ns
- , .		6	_	36	_			45	_		<u> </u>	54			
		2		250	_	_	_	315	_	[—	_	375	-	—	<u> </u>
Ē→Y, Ÿ	t _{PLH}	4.5	_	50		54	-	63	-	68		75	-	81	ns
_ ,,,	t _{PHL}	6	_	43	_			54	-			64	_		
		2	1-	260		-	-	325	_	-	_	390	_	-	
$Sn \rightarrow Y, \overline{Y}$	t _{PLH}	4.5	_	52	_	59		65	-	74	-	78	-	89	ns
J., .	t _{PHL}	6	_	44	_	_	_	55	<u> </u>	_		66		_	
	<u> </u>	2	_	290	_	_	_	365	I –	T		435	_		
ĪĒ → Υ, Ϋ	t _{PLH}	4.5	_	58	_	63	-	73		79	-	87	—	94	ns
 1, 1	tehl	6	_	49	_		-	62		<u> </u>		74	l		l
Output Disabling	 	2	 _	155	T -	T-	_	195	Τ-	 -	T —	235	-	_	
Time		4.5	_	31	_	33	-	39	-4	41	-	47	—	50	
OEn to Y, Y	telZ	6	_	26	_	_	i —	33	38	5-	_	40		<u> </u>	ns
OLITIO 1, 1	-	2	_	155	T_	T -		195	-		_	235	-	-	113
OE3 to Y, ₹	tpHZ	4.5		31	_	39	3	39	1 -	49	-	47	_	59	
023101,1		6	_	26	_	400	X	33		-	-	40	-	-	L .
Output Enabling	ļ	2		150	4	W.	-	190	-	-	Τ-	225		-	
Time		4.5	_	30	_	34	-	38	-	43	-	45		51	
OEn to Y, Y	tezu	6		26			V	33		_	_	38	-		ns
OEIIIO 1, 1	┥ .	2		160	_	_	-	200	-	1-	T-	240		T-	1115
OE3 to Y, \overline{Y}	t _{PZH}	4.5		32		34	_	40	_	43	_	48	_	51	
OE3 (0 1, 1		6		27	_	_	_	34	_	-	-	41			<u> </u>
		2	1	60	1_	t_		75	_	1-	1-	90	_	1-	
Output	tTLH	4.5		12	_	12	_	15	-	15	_	18	-	18	ns
Transition Time	t _{THL}	6	1 _	10	_	_	_	13	_	_	-	15		<u> </u>	
Input		-	1	 '`	1			T							1 _
Capacitance	Ci		_	10	-	10	-	10	-	10	-	10	-	10	pF
			1			1					 		1	1	
3-state															_
Output	Co		_	20		20	-	20		20	-	20	-	20	pF
Capacitance								1							1
Capacitation		1				1	1			1					1

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input I, I, = 6 ns) - HC/HCT356

	CL	CYMBOL	TYP	ICAL	UNITS	
CHARACTERISTIC	(pF)	SYMBOL	54/74HC	54/74HCT		
Propagation Delay $CP \rightarrow Y, \overline{Y}$	15	t _{PLH} , t _{PHL}	22	22	ns	
Sn→Y, ▼	15	t _{PLH} , t _{PHL}	22	25	ns	
LE →Y, Ÿ	15	t _{PLH} , t _{PHL}	24	25	ns	
Output Disabling Time	15	tplz, tpHZ	13	13, 15	ns	
Output Enabling Time	15	t _{PZL} , t _{PZH}	12, 13	14	ns	
Power Dissipation Capacitance*		CPD	51	52	pF	

^{*}CPD is used to determine the dynamic power consumption, per device

 $P_D = V_{CC}^2 f_i(C_{PD} + C_L)$ where:

f, = input frequency.

C_L = output load capacitance

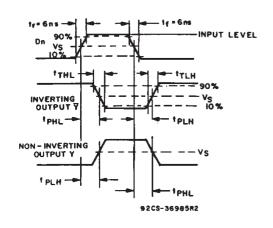
V_{cc} = supply voltage.

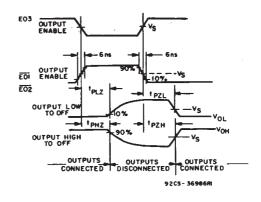
PREREQUISITE FOR SWITCHING FUNCTION — HC/HCT356

			3,	25	°C		-4	0°C to	o +85°	,C	-55°C to +125°C				
CHARACTERISTIC	SYMBOL	Vcc	Н	C	H	CT	74	HC	74t	1CT	54	нС	54H	1CT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	1
CP Pulse Width		2	80	_	_	_	100	_	_	T —	120	_	_	_	
	t _{PLH}	4.5	16	-	20		20		25	_	24	_	30	_	ns
	t _{PHL}	6	14			_	17			_	20	_			
LE Pulse Width		2	80	_			100	_	_	_	120	_	_		
	t _{PLH}	4.5	16	—	20	_	20	_	25		24		30	_	ns
	t _{PHL}	6	14		-		17	l —	_		20		_	l —	
Set Up Times		2	5		_		5		_	-	5	_		_	
Dn → CP	ts∪	4.5	5	_	7	_	5	_	9	—	5	_	11		пѕ
		6	5	_	_		5	_		_	5		_	_	
		2	5	_		_	5	_	_	_	5			_	
Sn → LE	t _{su}	4.5	5		7	_	5	_	9	_	5		11	-	ns
		6	5	-		_	5	_ 1		_	5	- 1	_	_	İ
Hold Times		2	45	_	_		55			_	70		_	_	
Dn → CP	t _n	4.5	9	—	9	_	-11		11		14		14		ns
		6	8		_	_	9	_	-A	减	12	_		_	
		2	60	_	_		75	_	<u> 3</u>	₽	90	<u></u>	_		
Sn → LE	t _h	4.5	12	_	12		15	3	15	_ (18	_	18	_	ns
		6	10		_		13		-4	Q*	15	-			

SWITCHING CHARACTERISTICS (CL - 50 pF, Input t, t = 6 ns) - HC/HCT356

				- 1				4			,				,
·				25	_			10°C	o +85°	,C	-5	5°C to	+125	°C_	
CHARACTERISTIC	SYMBOL	Vcc	H	IC 💮		CT	_	HC	74H	ICT	54	HC	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay:	telH	2	-	255	_ `	_	-	320		_		385	-	_	
CP →Y, \overline{Y}	t _{PHL}	4.5		51	_	51	_	64	_	64		77	_	77	ns
	(PHL	6	_	43			_	54		_	_	65	_		
_	t _{PLH}	2	_	260			_	325	-	-	_	390	_	_	
Sn → Y, \overline{Y}	t _{PHI}	4.5	_	52		59	-	65	-	74	—	78		89	ns
	UPHL.	- 6	<u> </u>	44				55		_		66			
	t _{PLH}	2	-	290	_	·	_	365	_	-	-	435	— ,	_	
ĪĒ →Υ, Ϋ́	t _{PHL}	4.5	—	58		63		73	_	79		87		94	ns
	TPHL	6		49			_	62	_		_	74			
Output Disabling			<u> </u>	155	—	—	_	195	-	-	_	235	—	-	
Time		2		31	_	33		39	_	41	_	47		50	
OE1, OE2 to Y, Y	t _{PLZ}	4.5		26				33	<u> </u>			40			กร
OE3 to Y, \overline{Y}	t _{PHZ}	6	_	155	<u> </u>			195	-			235			113
			-	31	_	37	—	39	-	46	-	47	—	56	
				26			_	33	<u> </u>			40			
Output Enabling			-	150	-	_		190	_	-		225	—		
Time		2	_	30	_	34	—	38	-	43	—	45	—	51	
OE1, OE2 to Y, Y	t _{PZL}	4.5		26				33				38			ns
OE3 to Y, Y	t _{PZH}	6	· —	160	_	—	—	200	—	-	—	240		—	1.0
			-	32	_	34		40	-	43	—	48		51	
				27				34				41			
Output	tTLH	2	-	60		_	_	75	-	_		90	_	-	
Transition Time	trec	4.5	-	12	_	12	_	15	-	15	_	18	_	18	ns
toput		6	<u> </u>	10				13				15			
Input						40									_
Capacitance	C,			10		10	-	10		10		10		10	pF
3-state															1
Output	Co			20	- :	20	_ :	20	_	20		20	_	20	ρF
Capacitance															





	54/74HC	54/74HCT
Input Level	V _{cc}	3 V
Vs	50% V _{CC}	1.3 V

Fig. 1 — Transition times and propagation delay times.

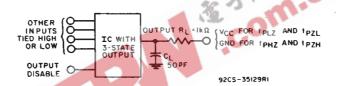


Fig. 2 — Three-state propagation delay test circuit.

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